

**REMARKS****A. Status of the Claims**

Claims 1 and 2 are pending in the application. Claims 1 and 2 were finally rejected under 35 USC 103(a) as being unpatentable over Mohsen et al., US Patent No. 4,881,114, in view of Zhang, US Patent No. 5,835,396.

**B. 35 USC 103(a) Rejection: Mohsen and Zhang; Claims 1 and 2**

Claims 1 and 2 were rejected under 35 USC 103(a) as being unpatentable over Mohsen et al. in view of Zhang.

As amended, claim 1 recites a three dimensional multi-level memory array disposed above a substrate, the array comprising: a first plurality of spaced-apart rail-stacks disposed at a first height in a first direction above the substrate; a second plurality of spaced-apart rail-stacks disposed above the first height and in a second direction different from the first direction; and a plurality of memory cells, each memory cell comprising a silicon nitride antifuse, wherein the antifuses are disposed at the intersections of the first rail-stacks and the second rail-stacks.

The device of Mohsen et al. does not teach memory cells having silicon nitride antifuses disposed at the intersections of first and second rail-stacks. Applicants respectfully request reconsideration.

### DISCUSSION OF CLAIM AMENDMENTS

Claim 1 has been amended to recite a three dimensional multi-level memory array disposed above a substrate, the array comprising a first plurality of spaced-apart rail-stacks disposed at a first height in a first direction above the substrate; a second plurality of spaced-apart rail-stacks disposed above the first height and in a second direction different from the first direction; and a plurality of memory cells, each memory cell comprising a silicon nitride antifuse, wherein the antifuses are disposed at the intersections of the first rail-stacks and the second rail-stacks. Support for this amendment can be found throughout the specification, for example at paragraph [0005], paragraph [0022], and in paragraphs [0026]-[0030].

Claim 2 has been amended to recite array of claim 1, further comprising polysilicon p+n- diodes or polysilicon p-n+ diodes. Support for this amendment can be found in paragraphs [0028], [0050], [0054], [0071], and [0076-0078], *inter alia*. None of these claim amendment constitutes new matter.

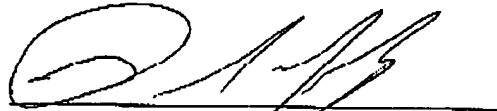
## CONCLUSION

In light of this response. Applicants believe this application to be in condition for allowance.

If there are any questions concerning this response, the Examiner is invited to contact the undersigned agent at (408) 869-2921.

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Respectfully submitted,



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